

4736B/4736BX

1024-BIT RANDOM ACCESS MEMORY WITH 3-STATE OUTPUTS

DESCRIPTION — The 4736B/4736BX is a 1024-Bit, Random Access Memory, organized 1024 words x 1 bit, with 3-state outputs. It has a Data Input (D), ten Address Inputs (A₀-A₉), an active LOW Write Enable Input (WE), an active LOW Chip Select Input (CS), and one 3-State Data Output (Q).

Information on the Data Input (D) is written into the memory location selected by the Address Inputs (A₀-A₉) when the Chip Select Input (CS) and the Write Enable Input (WE) are LOW. Under these conditions the Data Output (Q) is held in a high impedance OFF state. Information is read from the memory location selected by the Address Inputs (A₀-A₉) while CS is LOW and WE is HIGH. When CS is HIGH the Data Output (Q) is held in a high impedance OFF state. This allows other 3-state outputs to be wired together in a bus arrangement. The 4736B/4736BX offers fully static operation. The 4736B is specified to operate over a Power Supply Voltage Range of 5 ± 0.5 V. The 4736BX is specified to operate over a Power Supply Voltage Range of 4.5 V to 12.5 V.

- TYPICAL HOLDING VOLTAGE OF 1.5 V
- 3-STATE OUTPUTS
- ORGANIZATION — 1024 WORDS x 1 BIT
- ON-CHIP DECODING
- FULLY STATIC OPERATION
- LOW POWER DISSIPATION
- HIGH SPEED
- CHIP SELECT INPUT FOR EASY MEMORY EXPANSION

PIN NAMES

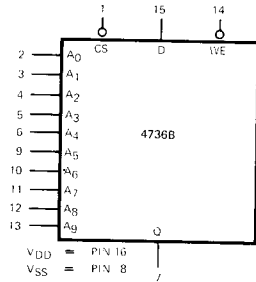
CS	Chip Select (Active LOW) Input
A ₀ -A ₉	Address Inputs
WE	Write Enable (Active LOW) Input
D	Data Input
Q	Data Output

MODE SELECTION

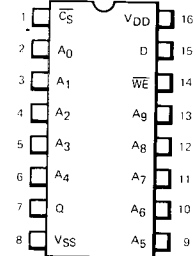
INPUTS		OUTPUT	MODE
CS	WE	Q	
H	X	High Impedance	Inhibit
L	L	High Impedance	Write
L	H	Data Written Into Memory	Read

H = HIGH Level
L = LOW Level
X = Don't Care

LOGIC SYMBOL

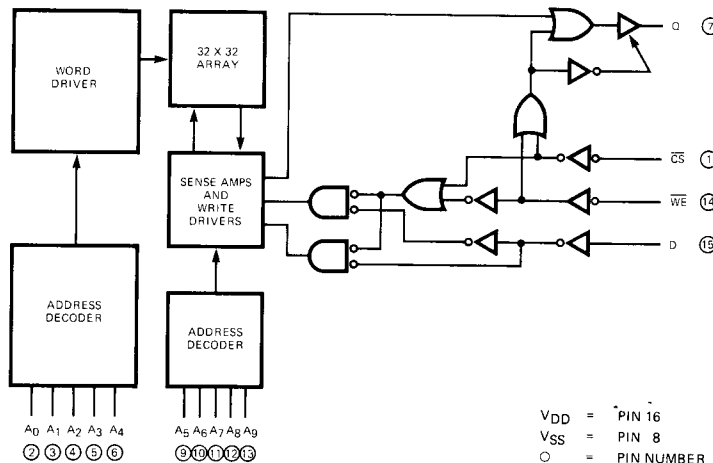


CONNECTION DIAGRAM DIP (TOP VIEW)



NOTE:
The Flatpak version has the same pinouts (Connection Diagram) as the Dual In-line Package.

BLOCK DIAGRAM



VDD = PIN 16
VSS = PIN 8
○ = PIN NUMBER

DC CHARACTERISTICS: V_{DD} as shown, $V_{SS} = 0$ V (See Note 1)

SYMBOL	PARAMETER		LIMITS									UNITS	TEMP	TEST CONDITIONS
			V _{DD} = 5 V			V _{DD} = 10 V			V _{DD} = 12.5 V					
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX			
I _{OZH}	Output OFF Current HIGH	XC									1.6 12	μA	MIN, 25°C MAX	Output Returned to V _{DD} , CS = V _{DD}
		XM									0.4 12		MIN, 25°C MAX	
I _{OZL}	Output OFF Current LOW	XC									-1.6 - 12	μA	MIN, 25°C MAX	Output Returned to V _{SS} , CS = V _{DD}
		XM									-0.4 - 12		MIN, 25°C MAX	
I _{DD}	Quiescent Power Supply Current	XC			32.5 250			65 500			130 1000	μA	MIN, 25°C MAX	CS = V _{DD} All inputs at 0 V or V _{DD}
		XM			8.75 250			17.5 500			35 1000		MIN, 25°C MAX	

AC CHARACTERISTICS AND SET-UP REQUIREMENTS: V_{DD} as shown, $V_{SS} = 0$ V, $T_A = 25^\circ\text{C}$ (See Note 2)

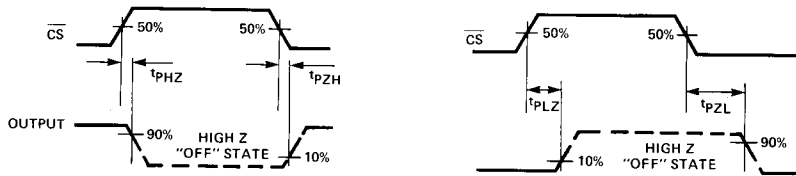
SYMBOL	PARAMETER	LIMITS									UNITS	TEST CONDITIONS
		V _{DD} = 5 V			V _{DD} = 10 V			V _{DD} = 12.5 V				
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		
t _{PLH}	READ MODE Propagation Delay, Address to Output		500			320			260		ns	C _L = 50 pF, R _L = 200 kΩ Input Transition Times ≤ 20 ns (R _L = 1 kΩ to V _{SS}) (R _L = 1 kΩ to V _{DD}) (R _L = 1 kΩ to V _{SS}) (R _L = 1 kΩ to V _{DD}) <

NOTES:

- Additional DC Characteristics are listed in this section under 4000B Series CMOS Family Characteristics.
- Propagation Delays and Output Transition Times are graphically described in this section under 4000B Series CMOS Family Characteristics.

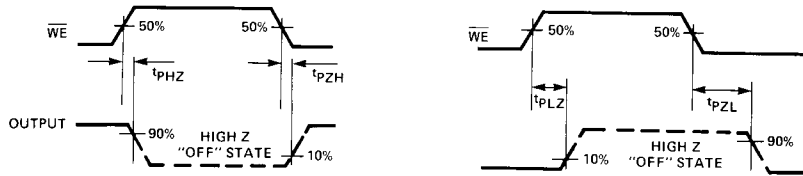
AC WAVEFORMS

READ MODE

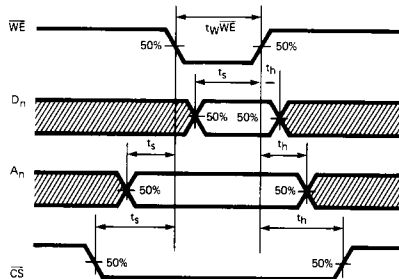


$\overline{CS}$ TO OUTPUT ENABLE AND DISABLE TIMES

WRITE MODE



$\overline{WE}$ TO OUTPUT ENABLE AND DISABLE TIMES



MINIMUM $\overline{WE}$ PULSE WIDTH AND SET-UP AND HOLD TIMES,
 D_n TO $\overline{WE}$, A_n TO $\overline{WE}$, AND $\overline{CS}$ TO $\overline{WE}$

Note: Set-up and Hold Times are shown as positive values but may be specified as negative values.